

#### **30V P-Channel Enhancement Mode MOSFET**

Voltage

-30 V

Current

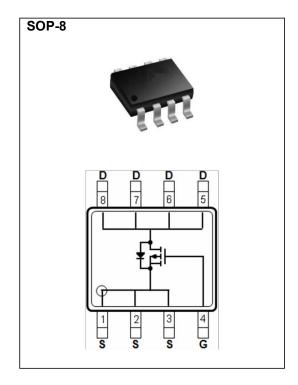
-15A

#### **Features**

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-10V, I<sub>D</sub>@-15A<19mΩ
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-4.5V, I<sub>D</sub>@-10A<14mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance

#### **Mechanical Data**

- Case: SOP-8 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0029 ounces, 0.083 grams



# Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-30	V	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Drain Current	T <sub>A</sub> =25°C		-15	Α	
	T <sub>A</sub> =70°C	l <sub>D</sub>	-10		
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	-48	Α	
Power Dissipation	T <sub>A</sub> =25°C	<b>D</b>	1.7	W	
	T <sub>A</sub> =70°C	P <sub>D</sub>	1.1		
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C	
Typical Thermal Resistance					
- Junction to Ambient (Note 5)	$R_{\theta JA}$	62.5	°C/W		



### **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V,I <sub>D</sub> =-15A	-	3	5	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-10A	-	7	9	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-15V, I <sub>D</sub> =-10A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	26	-	nC
Gate-Source Charge	$Q_{gs}$		-	8.7	-	
Gate-Drain Charge	$Q_{gd}$		-	8.6	-	
Input Capacitance	Ciss	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	3168	-	pF
Output Capacitance	Coss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	393	-	
Reverse Transfer Capacitance	Crss	I-I.UIVIIIZ	-	258	-	
Turn-On Delay Time	td <sub>(on)</sub>	\/ _ 45\/	-	11	-	
Turn-On Rise Time	tr	$V_{DS}$ =-15V, $I_{D}$ =-1A, $V_{GEN}$ =-10V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	14	-	ns
Turn-Off Delay Time	td <sub>(off)</sub>		-	102	-	
Turn-Off Fall Time	tf	, ,	-	47	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	la			-	-12	А
Diode Forward Current	Is	<b></b>	_			
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V	-	-0.7	-1.0	V

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial  $T_J$  =25°C.
- 5. R<sub>OJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.





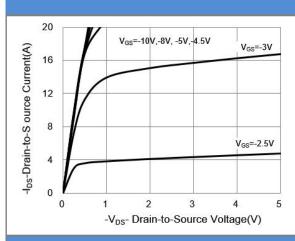
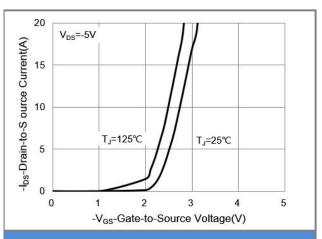


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

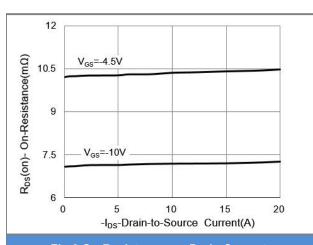


Fig.3 On-Resistance vs. Drain Current

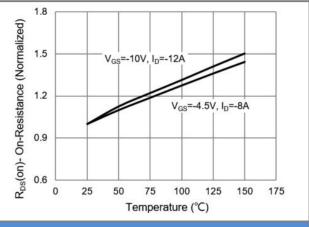


Fig.4 On-Resistance vs. Junction temperature

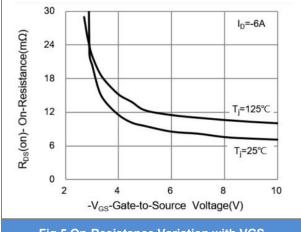
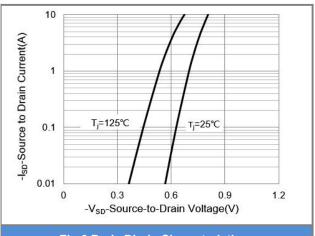


Fig.5 On-Resistance Variation with VGS.



**Fig.6 Body Diode Characteristics** 



#### **TYPICAL CHARACTERISTIC CURVES**

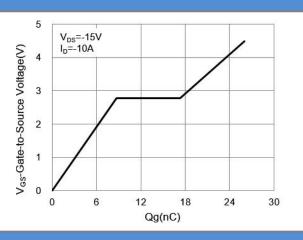


Fig.7 Gate-Charge Characteristics

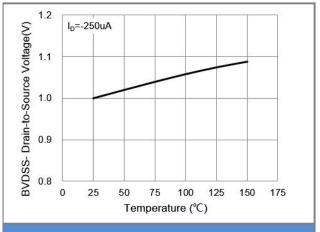


Fig.8 Breakdown Voltage Variation vs. Temperature

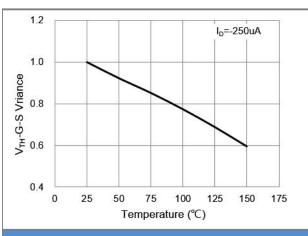


Fig.9 Threshold Voltage Variation with Temperature

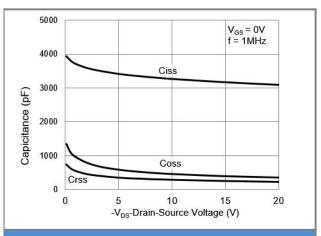


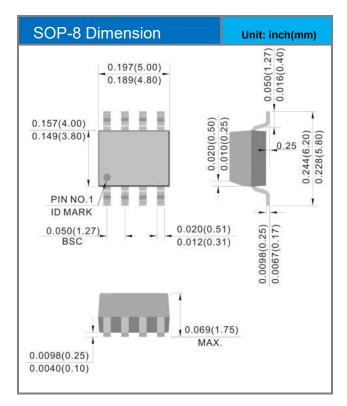
Fig.10 Capacitance vs. Drain-Source Voltage

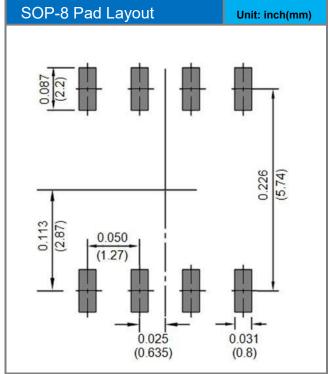


#### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type		
CSM320P15SOP8	SOP-8	2.5K pcs / 13" reel		

### **Packaging Information & Mounting Pad Layout**







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